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NPN resistor-equipped transistors; $R1 = 2.2 \text{ k}\Omega$, $R2 = 10 \text{ k}\Omega$ Rev. 04 — 16 November 2009Product data sh

Product data sheet

Product profile 1.

1.1 General description

NPN Resistor-Equipped Transistors (RET) family.

Type number	Package		PNP complement	
	NXP	JEITA	JEDEC	
PDTC123YE	SOT416	SC-75	-	PDTA123YE
PDTC123YK	SOT346	SC-59A	TO-236	PDTA123YK
PDTC123YM	SOT883	SC-101	-	PDTA123YM
PDTC123YS ^[1]	SOT54	SC-43A	TO-92	PDTA123YS
PDTC123YT	SOT23	-	TO-236AB	PDTA123YT
PDTC123YU	SOT323	SC-70	-	PDTA123YU

[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- General-purpose switching and amplification
- Inverter and interface circuits

1.4 Quick reference data

Table 2 Quick reference data

Reduces	pick	and	place	costs

Reduces component count

Circuit drivers

	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		3.6	4.5	5.5	



NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

2. Pinning information

Pin	Description	Simplified outline	Symbol
SOT54			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	1 2 001aab347	1 R2 006aaa145
SOT54A			
1	input (base)		
2	output (collector)		2
3	GND (emitter)	001aab348	1 R1 R2 006aaa145
SOT54 va	iriant		
1	input (base)		
2	output (collector)		B1 P1
3	GND (emitter)	U C C C C C C C C C C C C C C C C C C C	1 - R2 R2 006aaa145
SOT23; S	OT323; SOT346; SOT416		
1	input (base)	_	
2	GND (emitter)	3	3
3	output (collector)	12	1 R2 sym007
SOT883			
1	input (base)		
2	GND (emitter)		
3	output (collector)	2 Transparent top view	

NPN resistor-equipped transistors; R1 = 2.2 k Ω , **R2 = 10** k Ω

3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
PDTC123YE	SC-75	plastic surface mounted package; 3 leads	SOT416				
PDTC123YK	SC-59A	plastic surface mounted package; 3 leads	SOT346				
PDTC123YM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883				
PDTC123YS ^[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54				
PDTC123YT	-	plastic surface mounted package; 3 leads	SOT23				
PDTC123YU	SC-70	plastic surface mounted package; 3 leads	SOT323				

[1] Also available in SOT54A and SOT54 variant packages (see <u>Section 2</u> and <u>Section 9</u>).

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PDTC123YE	19
PDTC123YK	31
PDTC123YM	G7
PDTC123YS	TC123Y
PDTC123YT	*AL
PDTC123YU	*19

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

5. Limiting values

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
VI	input voltage					
	positive			-	+12	V
	negative			-	-5	V
lo	output current (DC)			-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1ms$		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT416		[1]	-	150	mW
	SOT346		[1]	-	250	mW
	SOT883		[2][3]	-	250	mW
	SOT54		[1]	-	500	mW
	SOT23		<u>[1]</u>	-	250	mW
	SOT323		<u>[1]</u>	-	200	mW
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60 µm copper strip line, standard footprint.

6. Thermal characteristics

Table 7.	Thermal characteristics	6				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	SOT416		<u>[1]</u> -	-	833	K/W
	SOT346		<u>[1]</u> -	-	500	K/W
	SOT883		[2][3]	-	500	K/W
	SOT54		<u>[1]</u> _	-	250	K/W
	SOT23		<u>[1]</u> -	-	500	K/W
	SOT323		<u>[1]</u> -	-	625	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB with 60 μ m copper strip line, standard footprint.

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

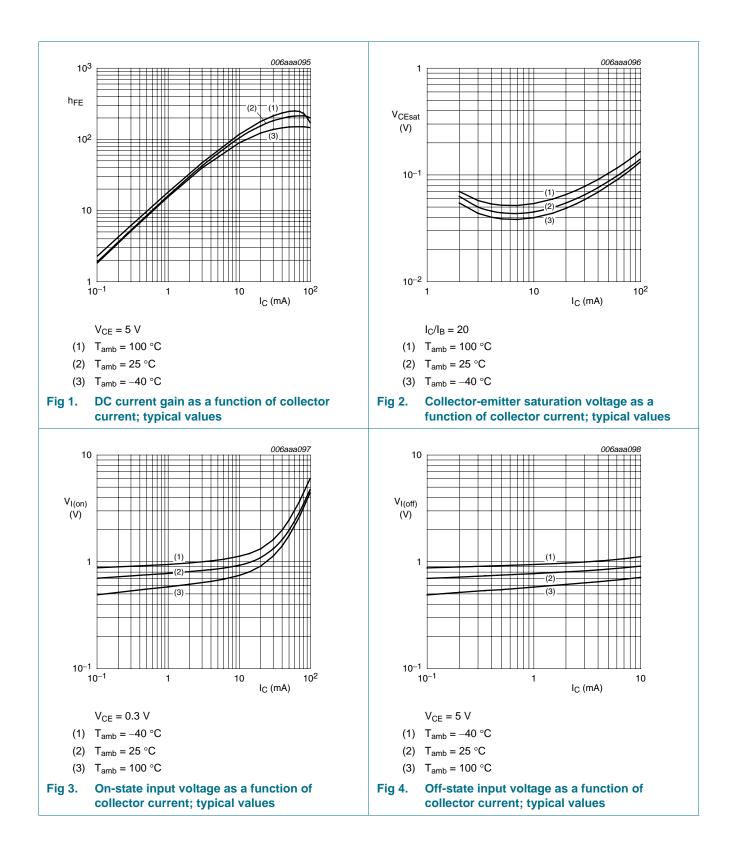
7. Characteristics

Table 8. $T_{amb} = 25$	Characteristics °C unless otherwise sp	ecified.				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$	-	-	1	μA
	cut-off current	$\label{eq:Vce} \begin{array}{l} V_{CE} = 30 \; V; \; I_{B} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 V; I_C = 0 A$	-	-	700	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	35	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} =10 mA; I_{B} = 0.5 mA	-	-	150	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_C = 100 μ A	-	0.75	0.3	V
V _{I(on)}	on-state input voltage	V_{CE} = 300 mV; I_{C} = 20 mA	2.5	1.15	-	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		3.6	4.5	5.5	
C _c	collector capacitance	V_{CB} = 10 V; I_E = i_e = 0 A; f = 1 MHz	-	-	2	pF

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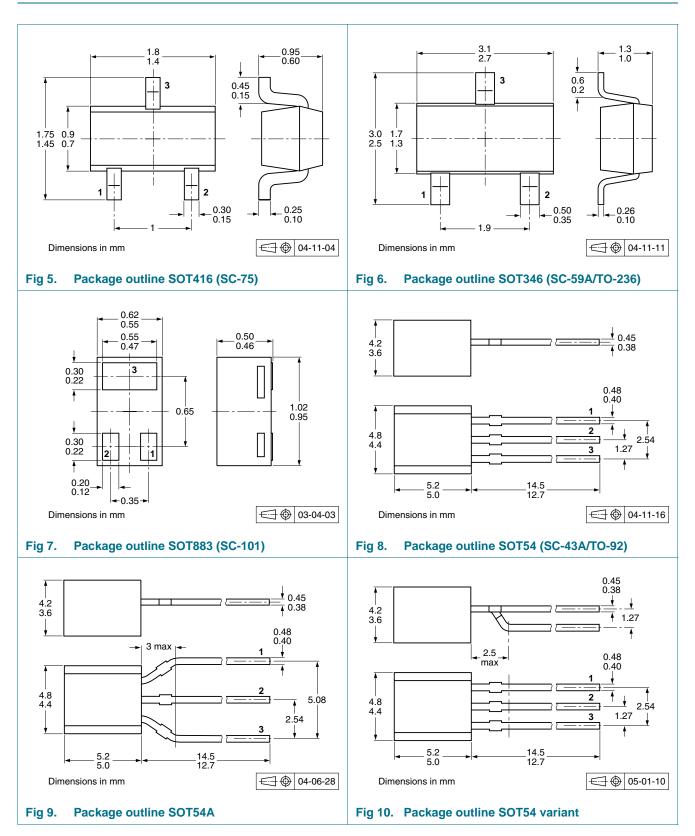
PDTC123Y series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω



NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

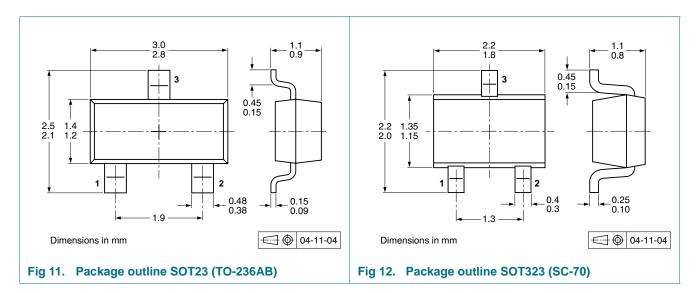
8. Package outline



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PDTC123Y series

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity			
			3000	5000	10000		
PDTC123YE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135		
PDTC123YK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135		
PDTC123YM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315		
PDTC123YS	SOT54	bulk, straight leads	-	-412	-		
	SOT54A	tape and reel, wide pitch	-	-	-116		
		tape ammopack, wide pitch	-	-	-126		
	SOT54 variant	bulk, delta pinning	-	-112	-		
PDTC123YT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235		
PDTC123YU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135		

[1] For further information and the availability of packing methods, see <u>Section 12</u>.

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

10. Revision history

Table 10. Revision his	story				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PDTC123Y_SER_4	20091116	Product data sheet	-	PDTC123Y_SER_3	
Modifications: • This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.					
PDTC123Y_SER_3	20050324	Product data sheet	-	PDTC123YT_2	
PDTC123YT_2	20040510	Objective data sheet	-	PDTC123YT_1	
PDTC123YT_1	20040406	Objective data sheet	-	-	

NPN resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 10 k Ω

11. Legal information

11.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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